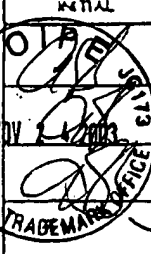


1 of 1

Form PTO-1449  <b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b> <i>(Use several sheets if necessary)</i>	<table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 50%;">           Document Number (Sequence)  <b>TSMC-02-428</b> </td> <td style="width: 50%;">           Application Number  <b>10/644,322</b> </td> </tr> <tr> <td colspan="2">           Applicant  <b>Chung - Shi Chiang et al.</b> </td> </tr> <tr> <td>           Filing Date  <b>08/20/03</b> </td> <td>           Group Art Unit         </td> </tr> </table>	Document Number (Sequence) <b>TSMC-02-428</b>	Application Number <b>10/644,322</b>	Applicant <b>Chung - Shi Chiang et al.</b>		Filing Date <b>08/20/03</b>	Group Art Unit
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Applicant <b>Chung - Shi Chiang et al.</b>							
Filing Date <b>08/20/03</b>	Group Art Unit						

### U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6246973	6/12/01	Sekine	703	4	8/12/99
	6378109	4/23/02	Young et al.	716	4	6/30/00
	6391668	5/21/02	Chacon et al.	438	17	5/1/00

### FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

### OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

- |       |   |
|-------|---|
| CIS - | "Hole Injection SiO <sub>2</sub> Breakdown Model for Very Low Voltage Lifetime Extrapolation," K.F. Schuegraf et al., IEEE Trans. Elec. Dev., Vol. 41(5), pp. 761-767, May 1994 |
| JS -  | "Modeling Gate and Substrate Currents due to Conduction - and - Valence-Band Electron and Hole Tunneling," W.C. Lee et al., 2000 Symposium VLSI Tech., pp. 198-199, 2000        |
| CIS - | "1.5nm Direct-Tunneling Gate Oxide Si MOSFET's," Hisayo Sakaki, Momose et al., IEEE Trans. Elec. Dev., Vol. 43(8) pp. 1233-1242, Aug. 1996.                                     |
| JS -  | "BSIM4 Gate Leakage Model Including Source-Drain Partition," K.M. Cao et al., 2000 IEDM, pp. 35.3.1 - 35.3.4.   |
| JS -  | Operation and Modeling of the MOS Transistor, Yannis P. Tsividis, McGraw Hill Book Co., NY, Copyright 1988, pp. 88-99.  |

EXAMINER

*Andie' Glwents*

DATE CONSIDERED

*09/02/04*

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.